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TABLE 1

Layer	**Material**	**Thickness (μm)**	**Dopant**	**Dopant Type**	**Doping Density (cm^{-3})**
1	GaAs	0.01	Be	p^+	1×10^{19}
2	$Al_{0.8}Ga_{0.2}As$	0.5	Be	p^+	2×10^{18}
3	$Al_{0.8}Ga_{0.2}As$	1.7	Undoped		$< 10^{15}$
4	$Al_{0.8}Ga_{0.2}As$	1	Si	n^+	2×10^{18}
5	GaAs	0.25	Si	n^+	2×10^{18}
Substrate	n^+ GaAs				